

1200V, 75A, Trench FS II Fast IGBT

General Description

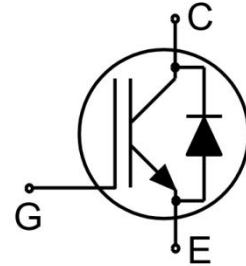
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1200V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology Offering
- Very low $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Welding



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE75TD120WW	TO-264	NCE75TD120WW



TO-264

Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	± 30	V
I_C	Collector Current	150	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	75	A
I_{Cpuls}	Pulsed Collector Current, t_p limited by T_{jmax}	300	A
-	turn off safe operating area, $V_{CE}=1200\text{V}$, $T_j=175^{\circ}\text{C}$	300	A
I_F	Diode Continuous Forward Current @ $T_C = 100^{\circ}\text{C}$	75	A
I_{FM}	Diode Maximum Forward Current	300	A
P_D	Power Dissipation @ $T_C = 25^{\circ}\text{C}$	833	W
	Power Dissipation @ $T_C = 100^{\circ}\text{C}$	417	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering	260	$^{\circ}\text{C}$

Thermal Characteristic

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.18	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	0.44	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

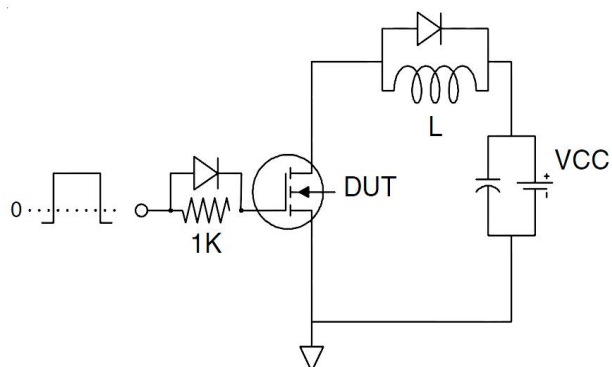
Symbol	Parameter	Test Conditions		Value			Units
				Min.	Typ.	Max.	
Static Characteristics							
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_{CE}=3mA$		1200	--	--	V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=1200V$		--	--	400	uA
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30V, V_{CE}=0V$		--	--	200	nA
$I_{GES(R)}$	Gate to Emitter Reverse Leakage	$V_{GE}=-30V, V_{CE}=0V$		--	--	200	nA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=75A$	$T_J=25^{\circ}C$	--	1.9	2.4	V
		$V_{GE}=15V$	$T_J=175^{\circ}C$	--	2.2	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=3mA, V_{CE}=V_{GE}$		4.5	--	6.5	V
Dynamic Characteristics							
C_{ies}	Input Capacitance	$V_{CE}=30V, V_{GE}=0V, f=1MHz$		--	13830	--	pF
C_{oes}	Output Capacitance			--	320	--	
C_{res}	Reverse Transfer Capacitance			--	280	--	
Q_g	Total Gate Charge	$V_{CC}=960V, I_C=75A, V_{GE}=15V$		--	450	--	nC
Q_{ge}	Gate to Emitter Charge			--	87	--	
Q_{gc}	Gate to Collector Charge			--	204	--	
Switching Characteristics							
$t_{d(ON)}$	Turn-on Delay Time	$V_{CE}=600V, I_C=75A, V_{GE}=0/15V, R_g=8\Omega$ Inductive Load		--	19	--	ns
t_r	Rise Time			--	17	--	
$t_{d(OFF)}$	Turn-Off Delay Time			--	170	--	
t_f	Fall Time			--	18	--	
E_{on}	Turn-On Switching Loss			--	5.5	--	mJ
E_{off}	Turn-Off Switching Loss			--	2.5	--	
E_{ts}	Total Switching Loss			--	8.0	--	

Electrical Characteristics of the Diode($T_c= 25^{\circ}\text{C}$ unless otherwise specified):

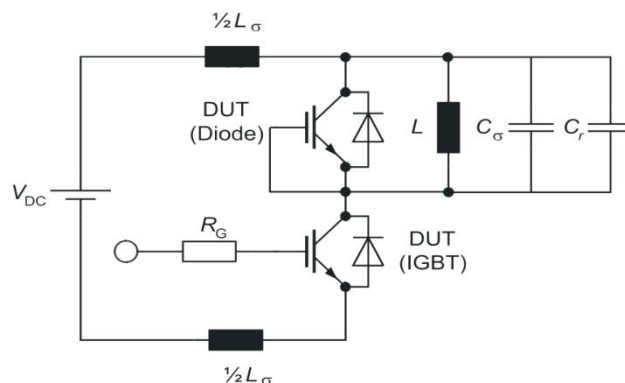
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{FM}	Diode Forward Voltage	I _F =37.5A	--	2.1	2.8	V
T _{rr}	Reverse Recovery Time	I _F =37.5A, di/dt=700A/us	--	150	--	ns
I _{RRM}	Diode Peak Reverse Recovery Current		--	10	--	A
Q _{rr}	Reverse Recovery Charge		--	0.75	--	uC
Pulse width t _{tp} ≤380μs,δ≤2%						

Test Circuit

1) Gate Charge Test Circuit

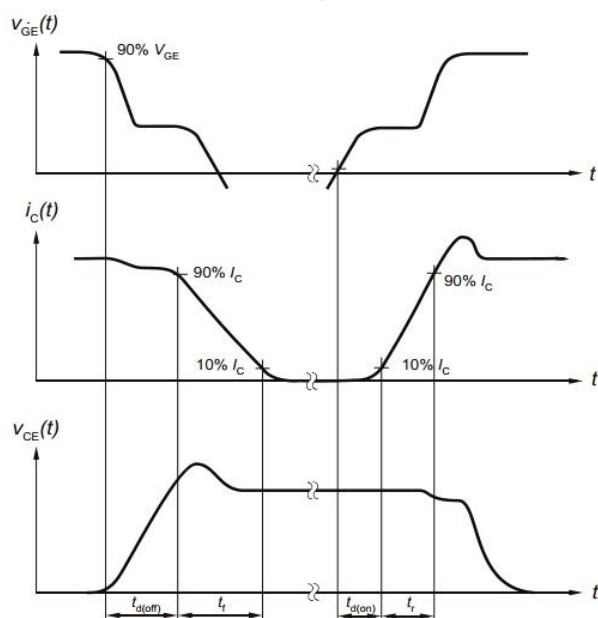


2) Switch Time Test Circuit

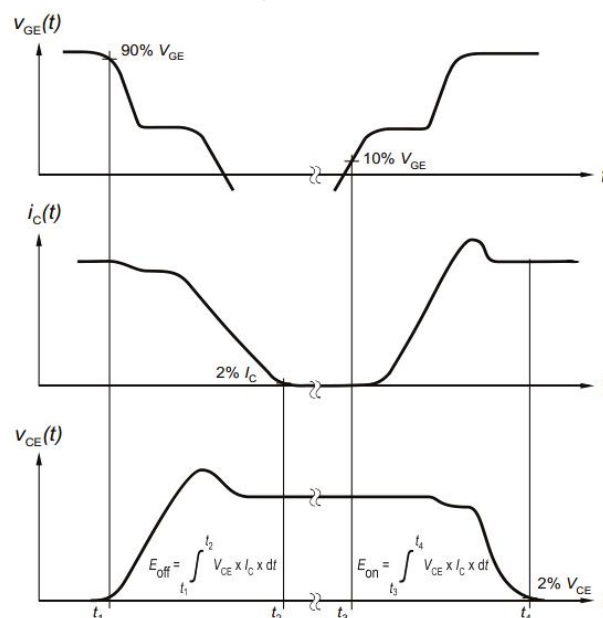


Switching characteristics

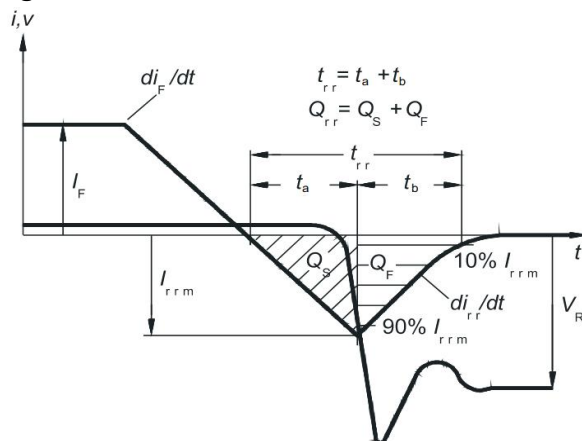
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

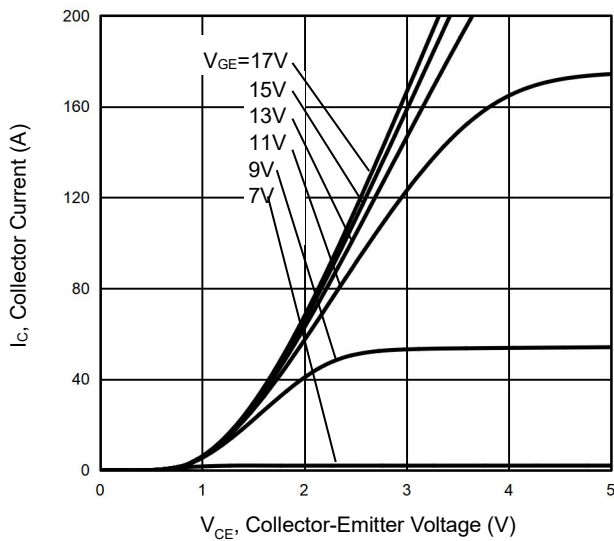


Figure 2 Transfer Characteristics

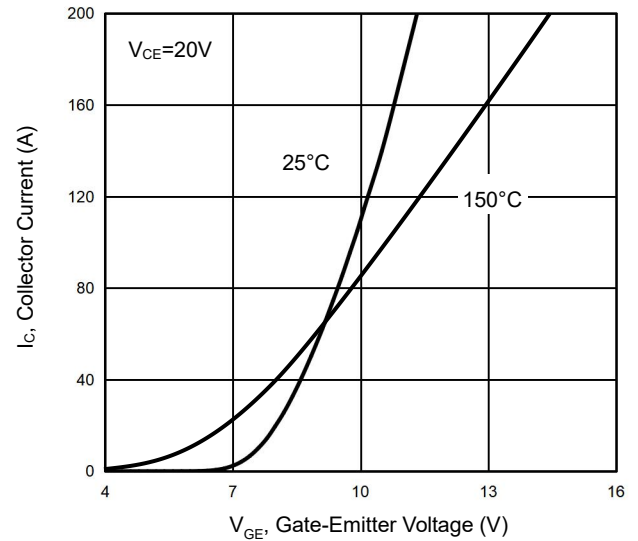


Figure 3 $V_{CE(sat)}$ vs. Case Temperature

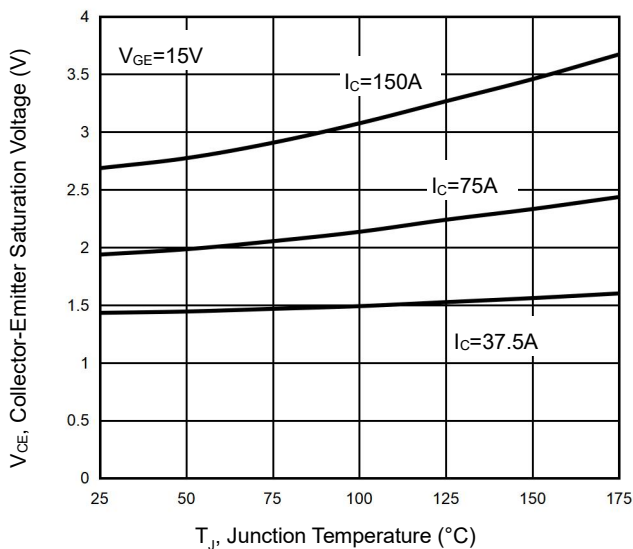


Figure 4 Saturation Voltage vs. V_{GE}

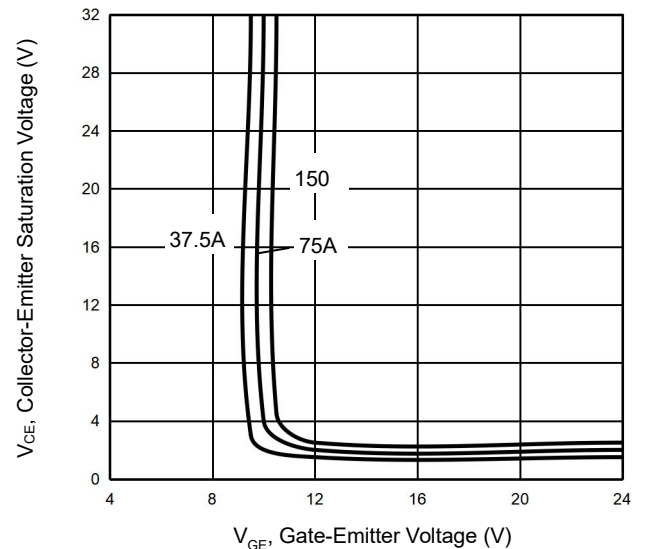


Figure 5 Capacitance Characteristics

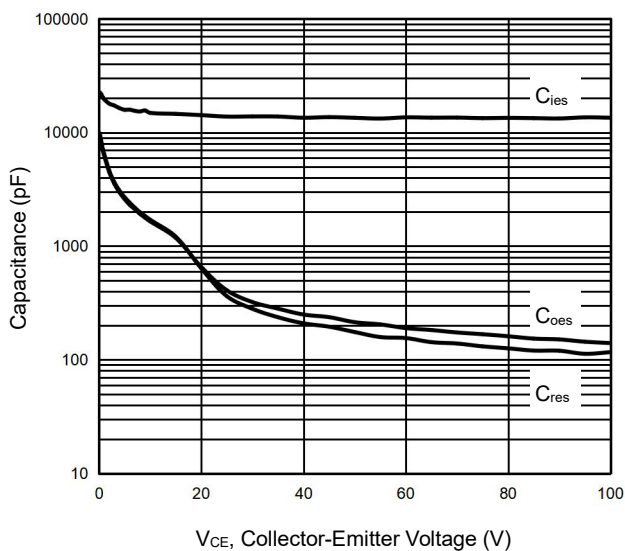
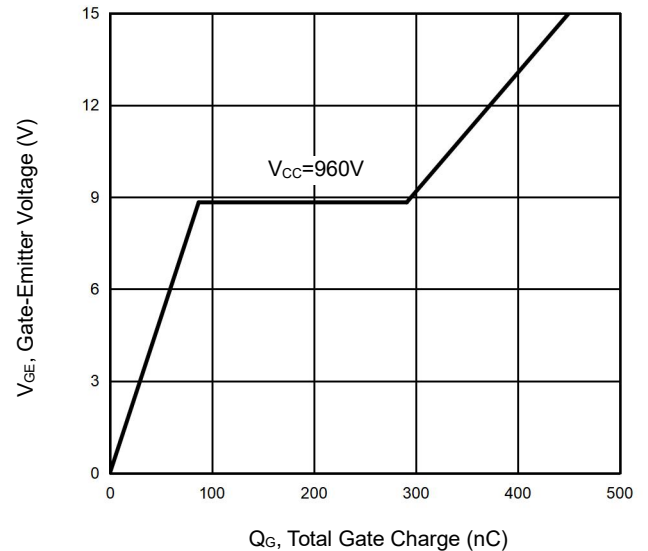


Figure 6 Gate Charge Wave Form



Typical Electrical and Thermal Characteristics

Figure 7 Forward Characteristics

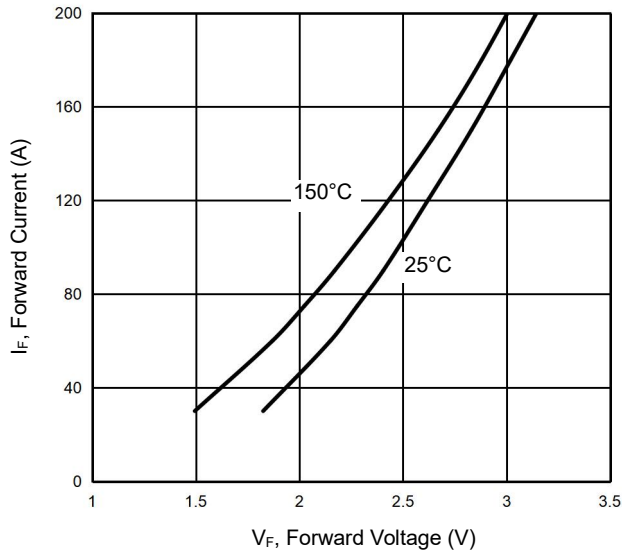


Figure 8 V_F vs. Temperature

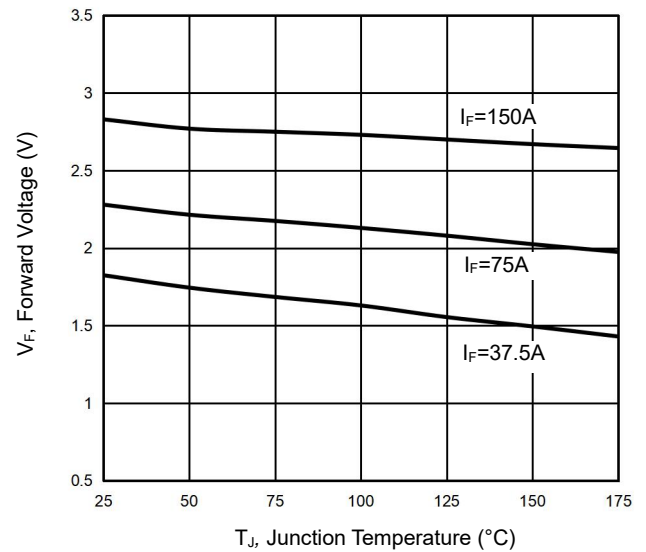


Figure 9 Switching Energy vs. Temperature

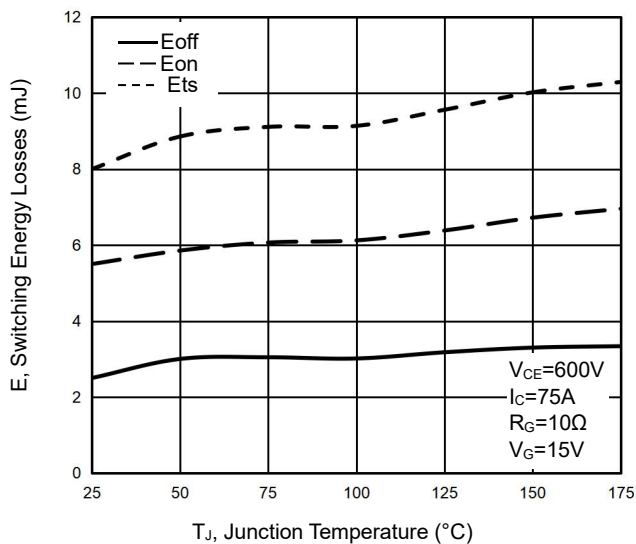


Figure 10 Forward Bias Safe Operating Area

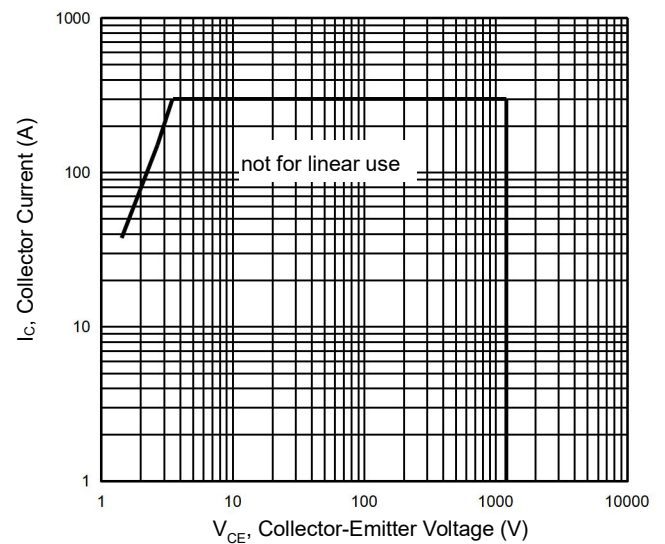


Figure 11 Gate-Emitter Threshold Voltage as a Function of Junction Temperature

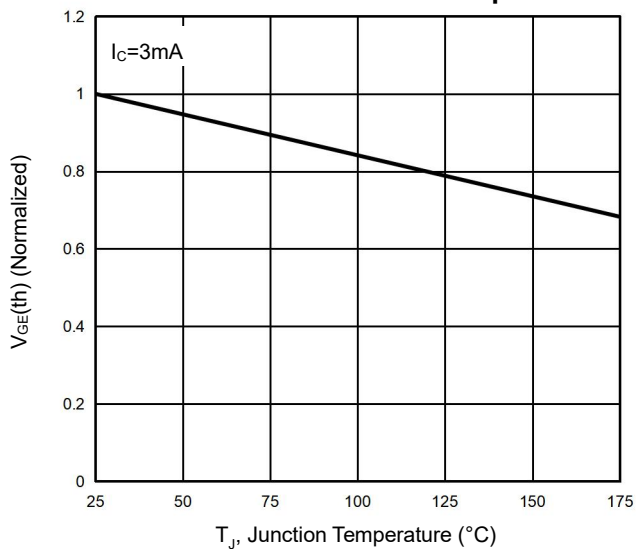
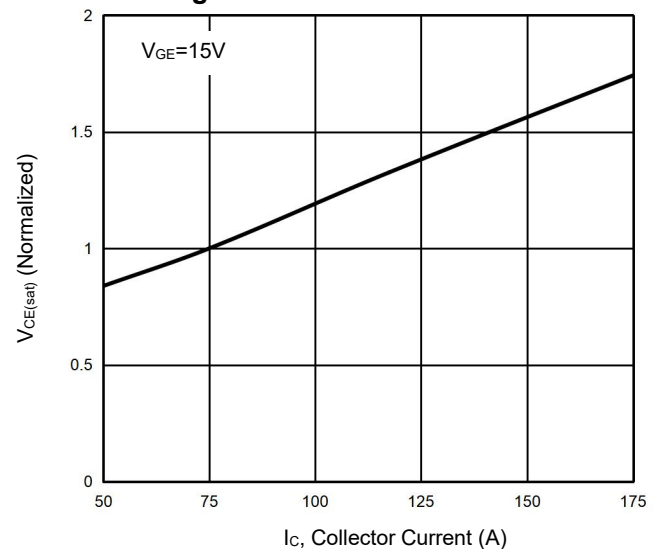


Figure 12 Typical Collector-Emitter Saturation Voltage as a function of Collector Current



Typical Electrical and Thermal Characteristics

Figure 13 Switching Loss vs. R_G

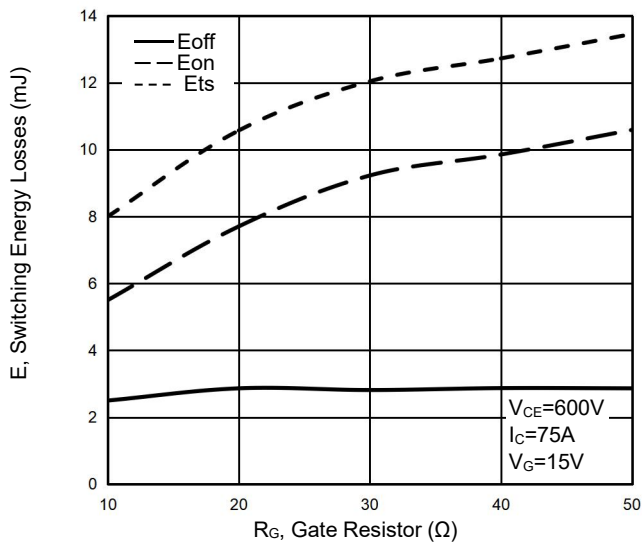


Figure 14 Switching Loss vs. Collector Current

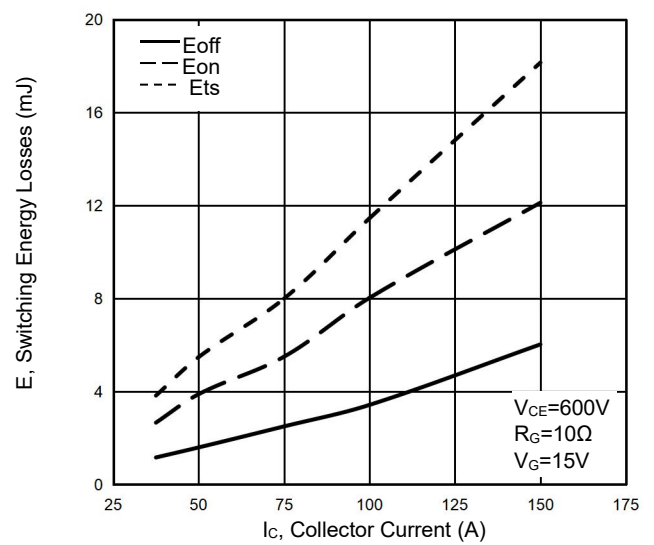


Figure 15 Switching Loss vs. Collector Current

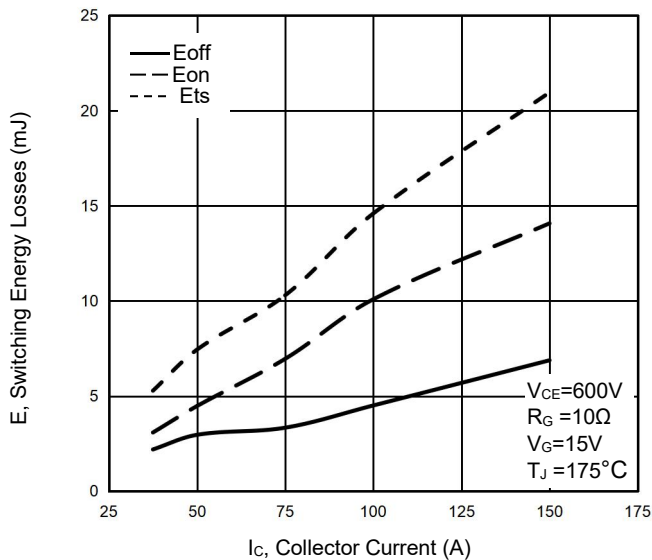


Figure 16 P_{tot} vs. Case Temperature

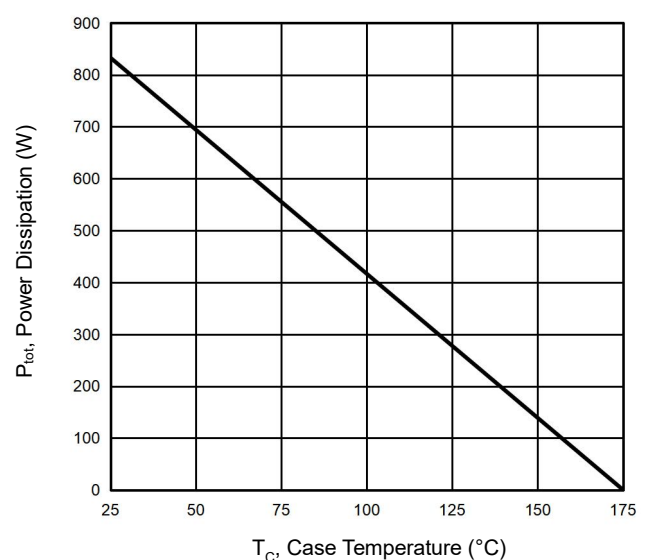


Figure 17 V_{CES} vs. Case Temperature

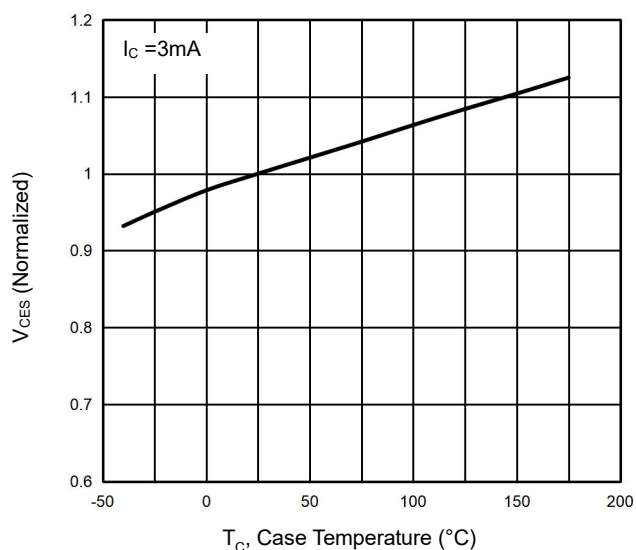
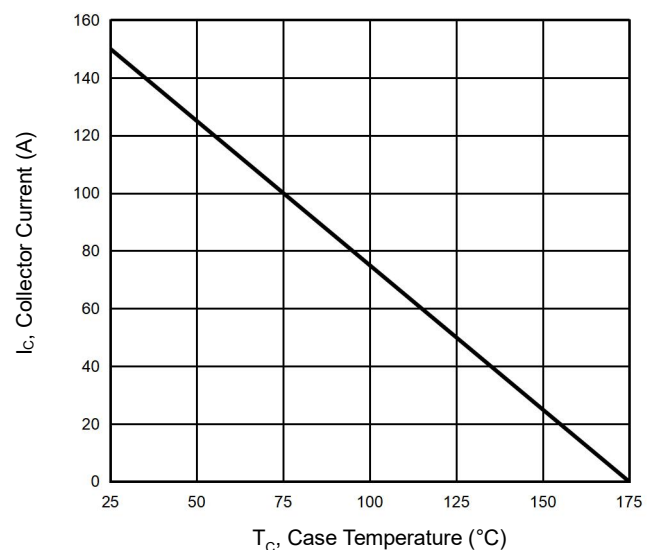
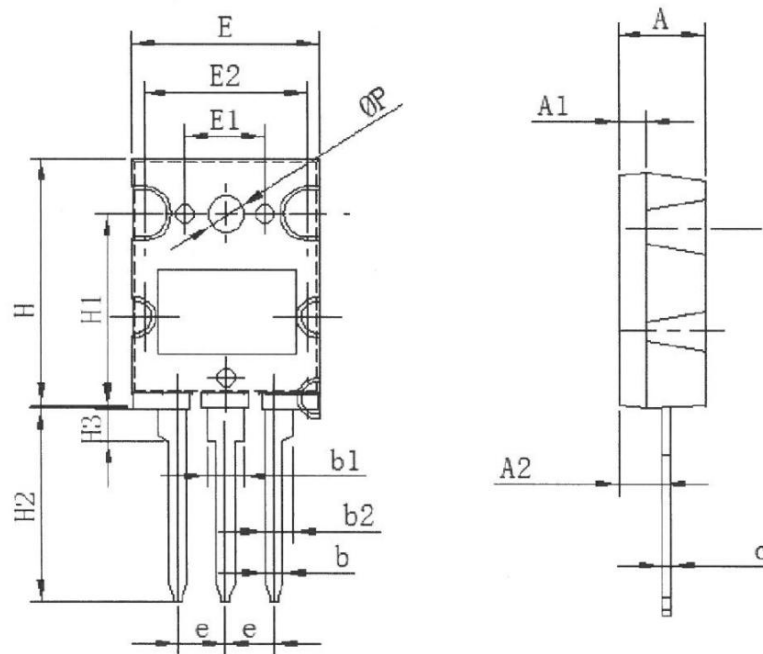


Figure 18 I_C vs. Temperature

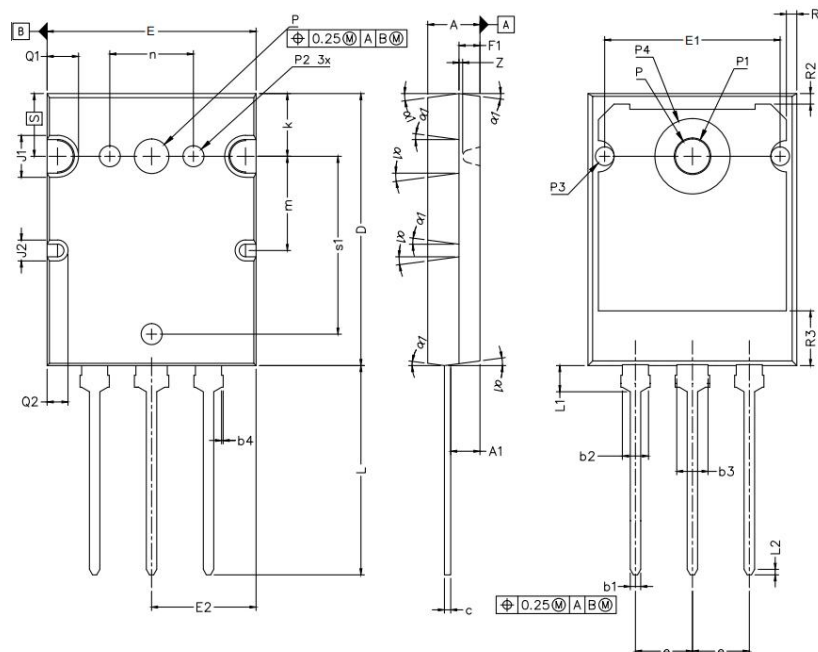


TO-264-d Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.80	5.20	0.18	0.20
A1	1.80	2.20	0.07	0.08
A2	3.20	3.60	0.12	0.14
b	0.80	1.20	0.03	0.04
b1	2.90	3.30	0.11	0.13
b2	2.40	2.80	0.09	0.11
c	0.50	0.70	0.02	0.03
e	5.25	5.65	0.20	0.22
E	19.80	20.20	0.78	0.79
E1	17.60	18.00	0.69	0.70
E2	8.60	9.00	0.33	0.35
H	25.80	26.20	1.01	1.03
H1	19.80	20.20	0.78	0.79
H2	19.80	20.80	0.78	0.81
H3	2.00	3.00	0.07	0.11
ΦP	3.00	3.40	0.11	0.13

TO-264-B Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.19	0.20
A1	2.60	3.00	0.10	0.12
b1	0.94	1.15	0.04	0.05
b2	2.35	2.65	0.09	0.10
b3	2.85	3.15	0.11	0.12
b4	--	0.20	--	0.01
c	0.55	0.75	0.02	0.03
D	25.80	26.20	1.02	1.03
E	19.80	20.20	0.78	0.80
E1	16.80 REF		0.66 REF	
E2	10.00 REF		0.39 REF	
e	5.35	5.55	0.21	0.22
F1	2.00 REF		0.08 REF	
J1	4.00 REF		0.16 REF	
J2	2.00 REF		0.08 REF	
k	6.00 REF		0.24 REF	
L	19.80	20.50	0.78	0.81
L1	2.40	2.59	0.09	0.10
L2	0.50 REF		0.02 REF	
m	9.00 REF		0.35 REF	
n	8.00 REF		0.31 REF	
P	3.20	3.40	0.13	0.14

P1	3.50 REF		0.14 REF	
P2	2.00 REF		0.08 REF	
P3	1.80 REF		0.07 REF	
P4	7.20 REF		0.28 REF	
Q1	3.00 REF		0.12 REF	
Q2	2.00 REF		0.08 REF	
R1	0.95	1.05	0.04	0.05
R2	0.90	1.10	0.04	0.05
R3	5.23 REF		0.21 REF	
S	6.00 BSC		0.24 BSC	
s1	17.00 REF		0.67 REF	
α1	7.5° REF			
Z	0.25	0.45	0.01	0.02

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